

★Under Development

8 Diode

Switching

Type No	Maximum Ratings				Electrical Characteristics (Ta = 25°C) MAX						Package	Fig
	V _{RM}	I _{FM}	I _O	P	V _F	I _F	I _R	V _R	C _T	t _{rr}		
	(V)	(mA)	(mA)	(mW)	(V)	(mA)	(μA)	(V)	(pF)	(ns)		
KDS1553	70				1.4	100	0.5	60	3.5		DO-35	F37
KDS1554	55	300	100	300				50				
KDS1555	35							30				
IN4148	75	225	100	500	1.0	10	0.025	20	4.0			
KDS176	35	300	100	300	1.2	100	0.5	30	3.0			
KDS181S											1-2HIA	F38
KDS184S											KDS 181S	KDS 184S
KDS187S											KDS 187S	KDS 190S
KDS190S											KDS 193S	KDS 196S
KDS193S											KDS 226S	KDS 200
KDS196S											KDS 201	KDS 227
★KDS226S	80	300	100	150	1.2	100	0.5	80	3.0	4		
KDS200				200					4.0			
KDS201												
★KDS227												

 $V_R = 6V$
 $R_L = 100\Omega$
 $I_F = 10mA$

Temperature Bias Compensation

Type No	V _R	I _{FM}	I _{FAV}	T _J	V _F			I _R		V _F		Package	Fig
					MIN	TYP	MAX	I _F	MAX	V _R	TYP		
KS8513A-0	5	150	50	150	0.63	0.65	0.68	3	10	5	-2.0	DO-35	F37
								(mA)	(μA)	(V)	mV/°C		

AFC diode

*Under Development

Type No	V _R (V)	T _J (°C)	MAX			Cr			K		Q 1~50MHZ		Package	Fig
			I _R (nA)	V _R (V)	MIN (PF)	MAX (PF)	VR (V)	f (MHZ)	MIN	MAX	TYP	V _r (V)		
*KDV147	15	125	50	15	11.7	13.7	8	1	—	—	—	—	TO-92M(C)	F5
*KDV149	15	125	50	15	—	30	8	1	—	—	450	1	TO-92M	F39
KDS2236	15	150	100	4	7	14	4	1	0.21	0.5	120	4	DO-35	F37

Schottky Barrier Diode

Type No	V _{RRM} (V)	I _{FRM} (A)	I _{FSM} (A)	I _{F(AV)} (A)	T _J (°C)	V _{F(Max)} (V) I _O =15A	I _R (mA) (Tc=25°C)	R _{th(J-C)} °C/W	R _{th(J-A)} °C/W	Package	Fig
KDB1545	45	15	150	7.5	-65~+150	0.70	0.1	3.0	60	TO-220AB(b)	F6

Rectifier

Type No	V _{RM} (V)	V _{RRM} (V)	I _O (A)	I _{SURGE} (A)	T _J (°C)	T _{sig} (°C)	V _F (V)	MAX I _F (A)	I _R (μA)	MAX V _{RRM} (V)	Package	Fig
IN4001	50	100	1	50	175	-65~175	1.1	1	10	RATED	DO-41	F36
IN4002	100	200		50								
IN4003	200	300		50								
IN4004	400	500		50								
IN4005	600	750		30								
IN4006	800	1000		30								
IN4007	1000	1200		30								